

Claims

[c1] 1.A pixel structure of an active matrix display device, the active matrix display device having a source of first potential and a source of second potential, the pixel structure comprising:

a storage capacitor;

a first active device having a first end electrically connected to a scanning line, a second end electrically connected to a data line, and a third end electrically connected to the storage capacitor; and

a plurality of active-type light emitting devices connected in parallel with each other, each of the active-type light emitting devices being electrically connected between the source of first potential, the source of second potential, and the third end.

[c2] 2.The pixel structure of claim 1, wherein the first active device is a first thin film transistor, and the first end is a gate electrode of the first thin film transistor, the second end is a drain electrode of the first thin film transistor, and the third end is a source electrode of the first thin film transistor.

[c3] 3.The pixel structure of claim 1, wherein the storage ca-

pacitor is electrically connected between the third end and a source of constant potential that is utilized for supplying a constant potential.

- [c4] 4.The pixel structure of claim 3, wherein the source of constant potential is the source of first potential.
- [c5] 5.The pixel structure of claim 1, wherein each of the active-type light emitting devices comprises:
 - a second active device having a fourth end connected to the third end, a fifth end connected to the source of first potential, and a sixth end; and
 - a light emitting device having a seventh end connected to the sixth end and an eighth end connected to the source of second potential.
- [c6] 6.The pixel structure of claim 5, wherein when an electrical shortage occurs in one of the light emitting devices, the pixel structure displays an image via the other light emitting devices.
- [c7] 7.The pixel structure of claim 5, wherein each of the second active devices comprises a second thin film transistor or a complementary metal–oxide semiconductor (CMOS).
- [c8] 8.The pixel structure of claim 7, wherein the fourth end is a gate electrode of the second thin film transistor, the

fifth end is a source electrode of the second thin film transistor, and the sixth end is a drain electrode of the second thin film transistor.

- [c9] 9. The pixel structure of claim 5, wherein each of the light emitting devices comprises an organic light emitting diode (OLED) or a light emitting diode (LED).
- [c10] 10. The pixel structure of claim 9, wherein the seventh end is an anode of the light emitting device, and the eighth end serves as a cathode of the light emitting device.
- [c11] 11. A nactive matrix display device comprising:
 - a plurality of scanning lines;
 - a plurality of data lines;
 - a plurality of pixels, each of the pixels comprising:
 - a storage capacitor;
 - a first active device having a first end electrically connected to the corresponding scanning line, a second end electrically connected to the corresponding data line, and a third end electrically connected to the storage capacitor; and
 - a plurality of active-type light emitting devices electrically connected in parallel with each other, each of the active-type light emitting devices being connected between a source of first potential, a source of second po-

tential, and the third end, each of the active-type light emitting devices comprising:

a light emitting device electrically connected to the source of second potential; and

a second active device having a fourth end electrically connected to the third end, a fifth end electrically connected to the source of first potential, and a sixth end electrically connected to the light emitting device.

- [c12] 12. The active matrix display device of claim 11, wherein the first active device is a first thin film transistor, and the first end is a gate electrode of the first thin film transistor, the second end is a drain electrode of the first thin film transistor, and the third end is a source electrode of the first thin film transistor.
- [c13] 13. The active matrix display device of claim 11, wherein the storage capacitor is electrically connected between the third end and a source of constant potential that is utilized for supplying a constant potential.
- [c14] 14. The active matrix display device of claim 13, wherein the source of constant potential is the source of first potential.
- [c15] 15. The active matrix display device of claim 11, wherein each of the second active devices comprises a second

thin film transistor or a complementary metal-oxide semiconductor (CMOS).

- [c16] 16.The active matrix display device of claim 15, wherein the fourth end is a gate electrode of the second thin film transistor, the fifth end is a source electrode of the second thin film transistor, and the sixth end is a drain electrode of the second thin film transistor.
- [c17] 17.The active matrix display device of claim 11, wherein each of the light emitting devices comprises an organic light emitting diode (OLED) or a light emitting diode (LED).
- [c18] 18.The active matrix display device of claim 11, wherein when an electrical shortage occurs in one of the light emitting devices of a pixel, the pixel displays an image via the other light emitting devices of the pixel.